PA-FOC

QUERY CONTROL FORM			RTIS USE ONLY	
Application No. 1008/199	Prepared by	Tw	Tracking Number	SEFIONS
Examiner-GAU GoudReau - 176	Date	3-31-04	Week Date	12-29-03
	No. of queries	1		

I the							
JACKET							
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449				
b. Applicant(s)	g. Disclaimer	I. Print Fig.	q. PTOL-85b				
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract				
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs				
e. Domestic Priority	i. Claims Allowed	o. PTO-892	t Other				

SPECIFICATION	MESSAGE
a. Page Missing	
b. Text Continuity	Figure & ir not dercribed on PAge 10
c. Holes through Data	
d. Other Missing Text	
e. Illegible Text	
f. Duplicate Text	
Brief Description	
h. Sequence Listing	
i. Appendix	
j. Amendments	
k. Other	
CLAIMS	
a. Claim(s) Missing	
b. Improper Dependency	Plene veery
c. Duplicate Numbers	Thort You
d. Incorrect Numbering	initials Tuy
e. Index Disagrees	RESPONSE
f. Punctuation	
g. Amendments	Corrected.
h. Bracketing	
i. Missing Text	
j. Duplicate Text	
k. Other	
	initials 724

Brief Description of the Drawings

The foregoing and further and more specific objects and advantages of the present invention will become readily apparent to those skilled in the art from the following detailed description of a preferred embodiment thereof taken in conjunction with the drawings, in which:

TOURTHUR BUILT

5

FIGs. 1-7 illustrate cross-sectional views of the steps in fabricating a tiered structure according to the present invention.

10

Detailed Description of the Preferred Embodiments

15

20

In developing a tiered structure, such as a T-gate structure, according to the present invention, the challenge lies in creating a tiered structure using only positive resists composed of polymeric materials having a low to medium molecular weight. In order to accomplish this, several issues must be overcome. First, resist compatibility must be taken into account. Low to medium molecular weight (MW) i-line and deep ultra violet (DUV) resists tend to intermix when other layers are coated on top of them. Use of these resists as the bottom resist layer must somehow avoid intermixing. resist/developer compatibility must be examined. Resists and developers must be chosen in such a way to affect only the layer(s) intended. Third, bake temperature compatibility must be dealt with. As the stack is built, care

25